

# FDB44N25

## N-Channel UniFET™ MOSFET

250 V, 44 A, 69 mΩ

### Features

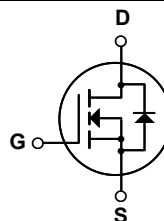
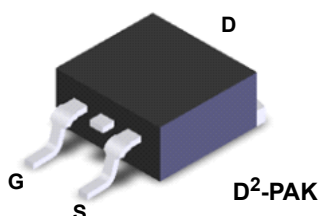
- $R_{DS(on)}$  = 69 mΩ (Max.) @  $V_{GS}$  = 10 V,  $I_D$  = 22 A
- Low Gate Charge (Typ. 47 nC)
- Low  $C_{rss}$  (Typ. 60 pF)
- 100% Avalanche Tested

### Applications

- PDP TV
- Lighting
- Uninterruptible Power Supply
- AC-DC Power Supply

### Description

UniFET™ MOSFET is Fairchild Semiconductor®'s high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.



### Absolute Maximum Ratings

Symbol	Parameter		FDB44N25	Unit
$V_{DSS}$	Drain-Source Voltage		250	V
$I_D$	Drain Current	- Continuous ( $T_C = 25^\circ\text{C}$ )	44	A
		- Continuous ( $T_C = 100^\circ\text{C}$ )	26.4	A
$I_{DM}$	Drain Current	- Pulsed (Note 1)	176	A
$V_{GSS}$	Gate-Source voltage		$\pm 30$	V
$E_{AS}$	Single Pulsed Avalanche Energy	(Note 2)	2055	mJ
$I_{AR}$	Avalanche Current	(Note 1)	44	A
$E_{AR}$	Repetitive Avalanche Energy	(Note 1)	30.7	mJ
$dv/dt$	Peak Diode Recovery $dv/dt$	(Note 3)	4.5	V/ns
$P_D$	Power Dissipation	( $T_C = 25^\circ\text{C}$ )	307	W
		- Derate above $25^\circ\text{C}$	2.45	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature Range		-55 to +150	$^\circ\text{C}$
$T_L$	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		300	$^\circ\text{C}$

### Thermal Characteristics

Symbol	Parameter	FDB44N25	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.41	$^\circ\text{C/W}$
$R_{\theta JA}^*$	Thermal Resistance, Junction-to-Ambient*	40	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	

\* When mounted on the minimum pad size recommended (PCB Mount)

## Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDB44N25	FDB44N25TM	D2-PAK	330mm	24mm	800

## Electrical Characteristics T<sub>C</sub> = 25°C unless otherwise noted

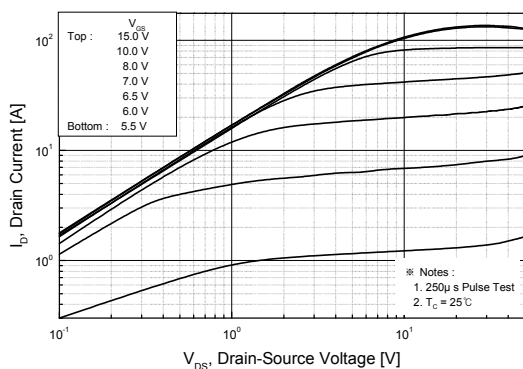
Symbol	Parameter	Conditions	Min.	Typ.	Max	Unit
Off Characteristics						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	250	--	--	V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250μA, Referenced to 25°C	--	0.25	--	V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 250V, V <sub>GS</sub> = 0V V <sub>DS</sub> = 200V, T <sub>C</sub> = 125°C	-- --	-- --	1 10	μA μA
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30V, V <sub>DS</sub> = 0V	--	--	100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30V, V <sub>DS</sub> = 0V	--	--	-100	nA
On Characteristics						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	3.0	--	5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 22A	--	0.058	0.069	Ω
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 40V, I <sub>D</sub> = 22A	--	32	--	S
Dynamic Characteristics						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1.0MHz	--	2210	2870	pF
C <sub>oss</sub>	Output Capacitance		--	450	585	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		--	60	90	pF
Switching Characteristics						
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 125V, I <sub>D</sub> = 44A R <sub>G</sub> = 25Ω  (Note 4)	--	55	120	ns
t <sub>r</sub>	Turn-On Rise Time		--	400	810	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		--	85	180	ns
t <sub>f</sub>	Turn-Off Fall Time		--	115	240	ns
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> = 200V, I <sub>D</sub> = 44A V <sub>GS</sub> = 10V  (Note 4)	--	47	61	nC
Q <sub>gs</sub>	Gate-Source Charge		--	18	--	nC
Q <sub>gd</sub>	Gate-Drain Charge		--	24	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current		--	--	44	A
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current		--	--	176	A
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0V, I <sub>S</sub> = 44A	--	--	1.4	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0V, I <sub>S</sub> = 44A	--	195	--	ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI <sub>F</sub> /dt =100A/μs	--	1.8	--	μC

### NOTES:

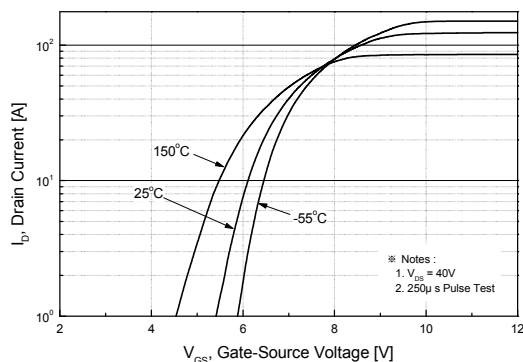
1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. L = 1.7mH, I<sub>AS</sub> = 44A, V<sub>DD</sub> = 50V, R<sub>G</sub> = 25Ω, Starting T<sub>J</sub> = 25°C
3. I<sub>SD</sub> ≤ 44A, di/dt ≤ 200A/μs, V<sub>DD</sub> ≤ BV<sub>DSS</sub>, Starting T<sub>J</sub> = 25°C
4. Essentially Independent of Operating Temperature Typical Characteristics

## Typical Performance Characteristics

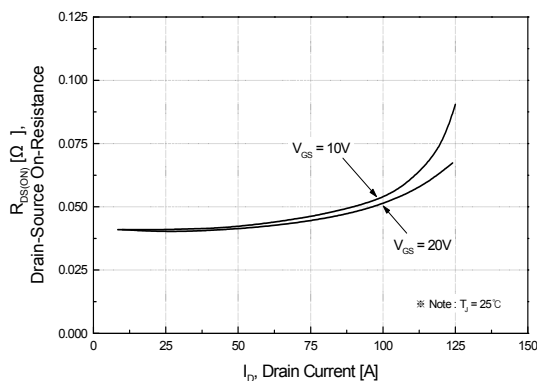
**Figure 1. On-Region Characteristics**



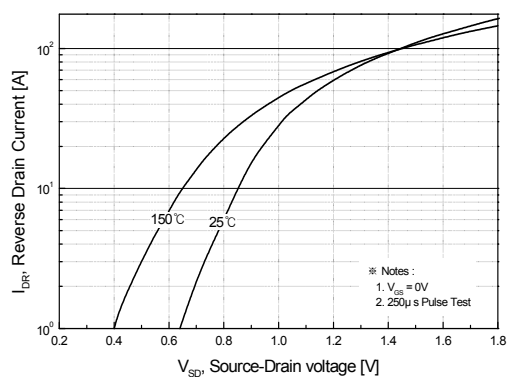
**Figure 2. Transfer Characteristics**



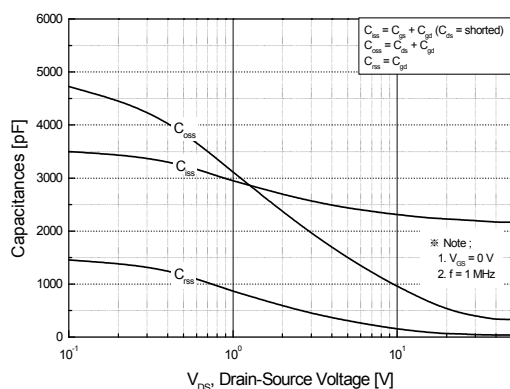
**Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage**



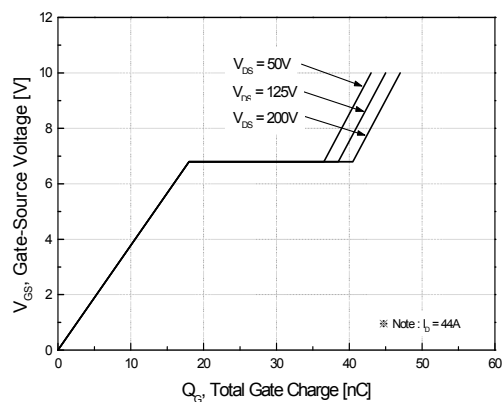
**Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature**



**Figure 5. Capacitance Characteristics**

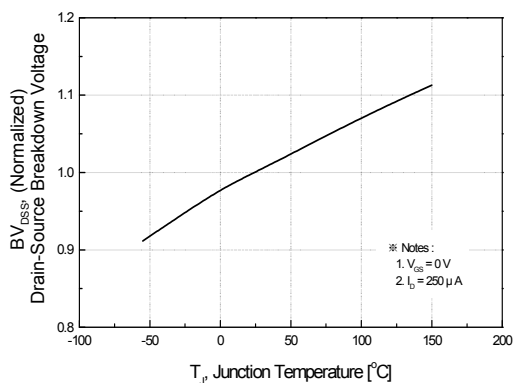


**Figure 6. Gate Charge Characteristics**

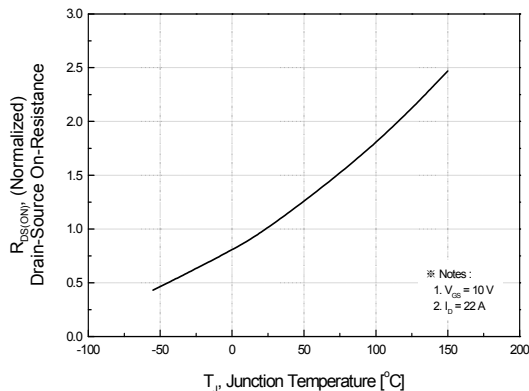


## Typical Performance Characteristics (Continued)

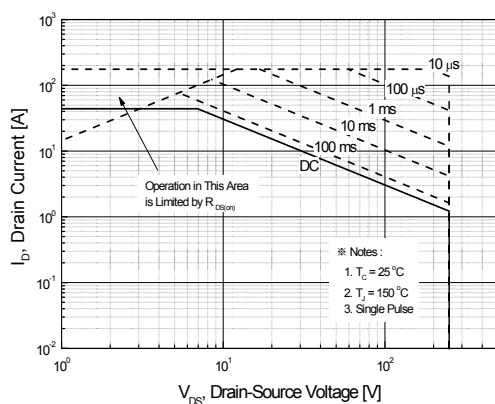
**Figure 7. Breakdown Voltage Variation vs. Temperature**



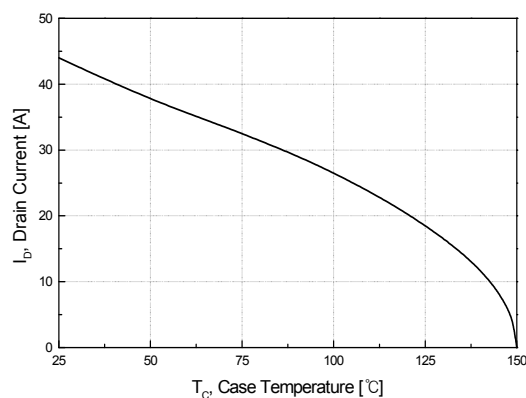
**Figure 8. On-Resistance Variation vs. Temperature**



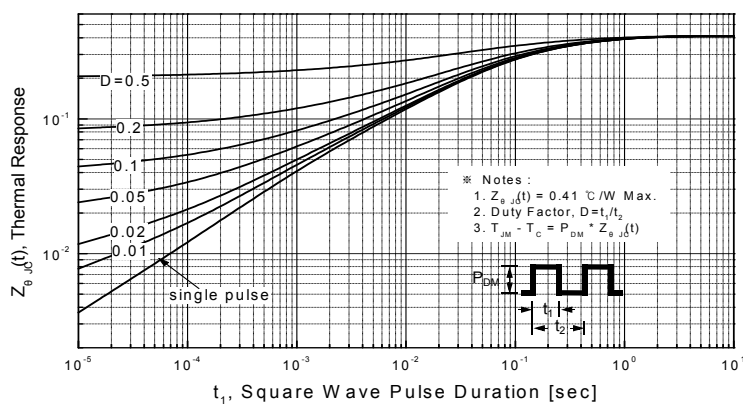
**Figure 9. Maximum Safe Operating Area**



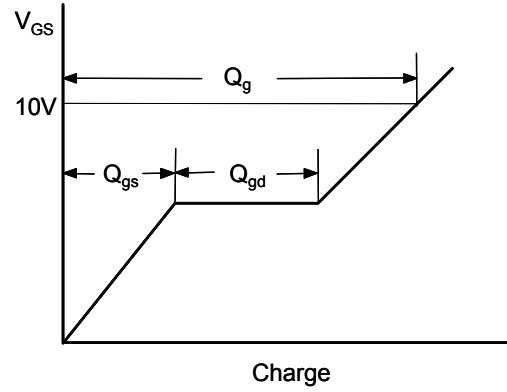
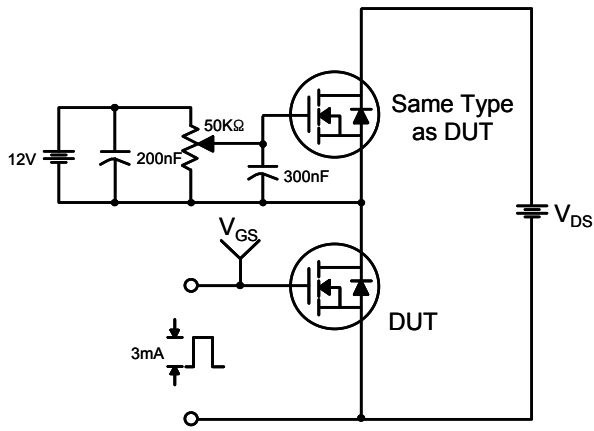
**Figure 10. Maximum Drain Current vs. Case Temperature**



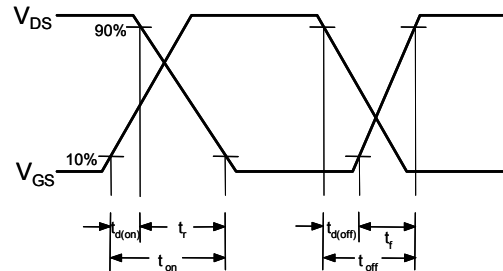
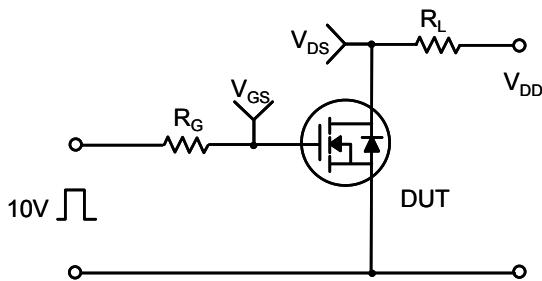
**Figure 11. Transient Thermal Response Curve**



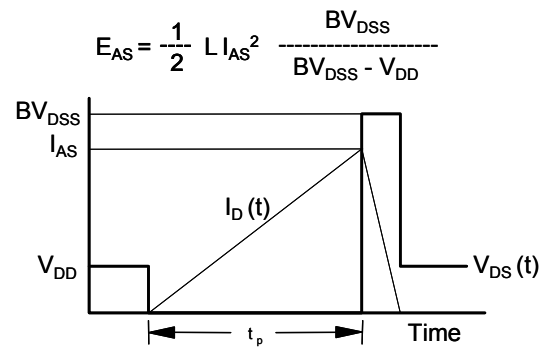
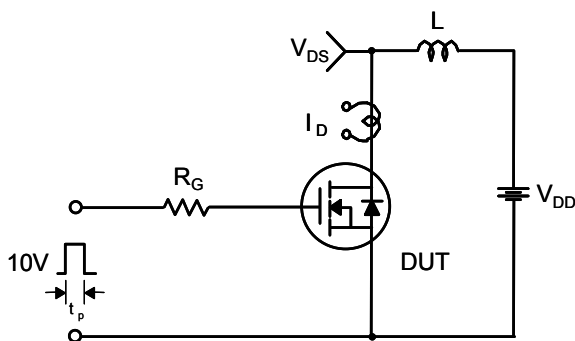
### Gate Charge Test Circuit & Waveform



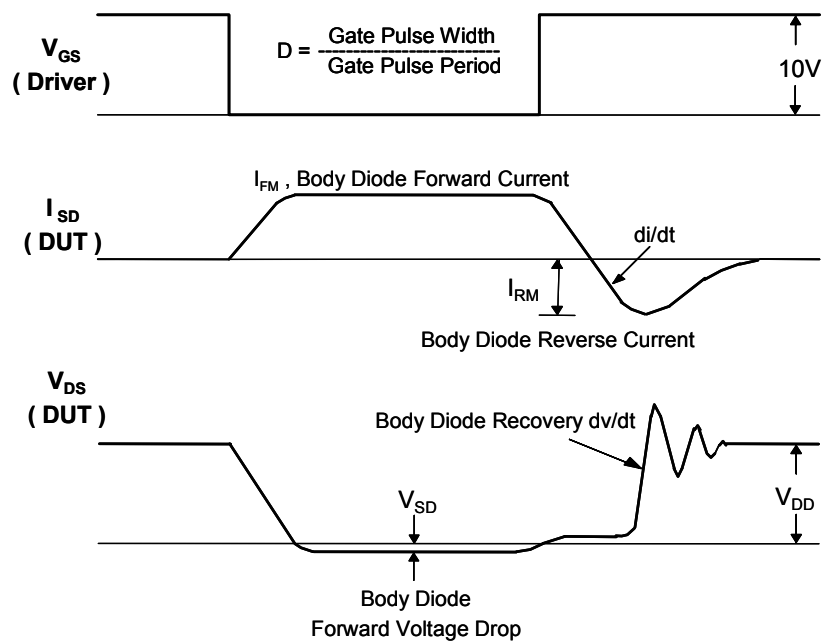
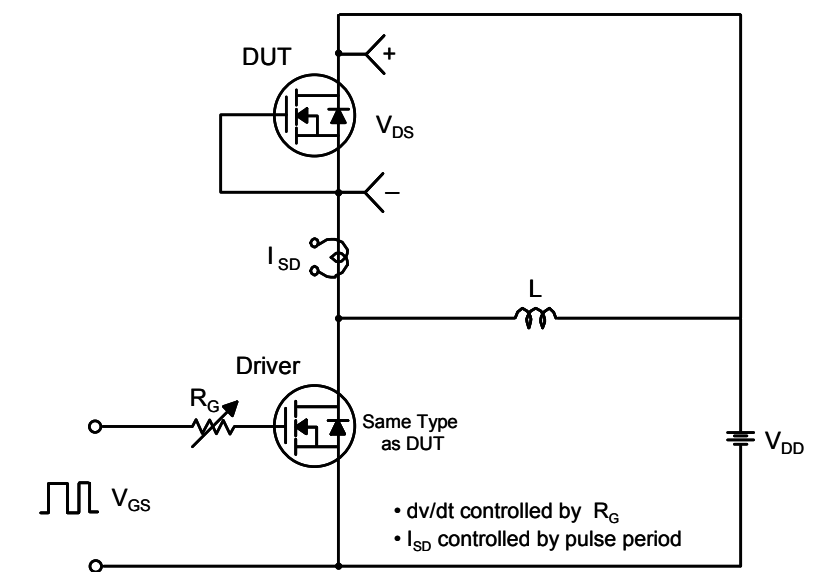
### Resistive Switching Test Circuit & Waveforms



### Unclamped Inductive Switching Test Circuit & Waveforms

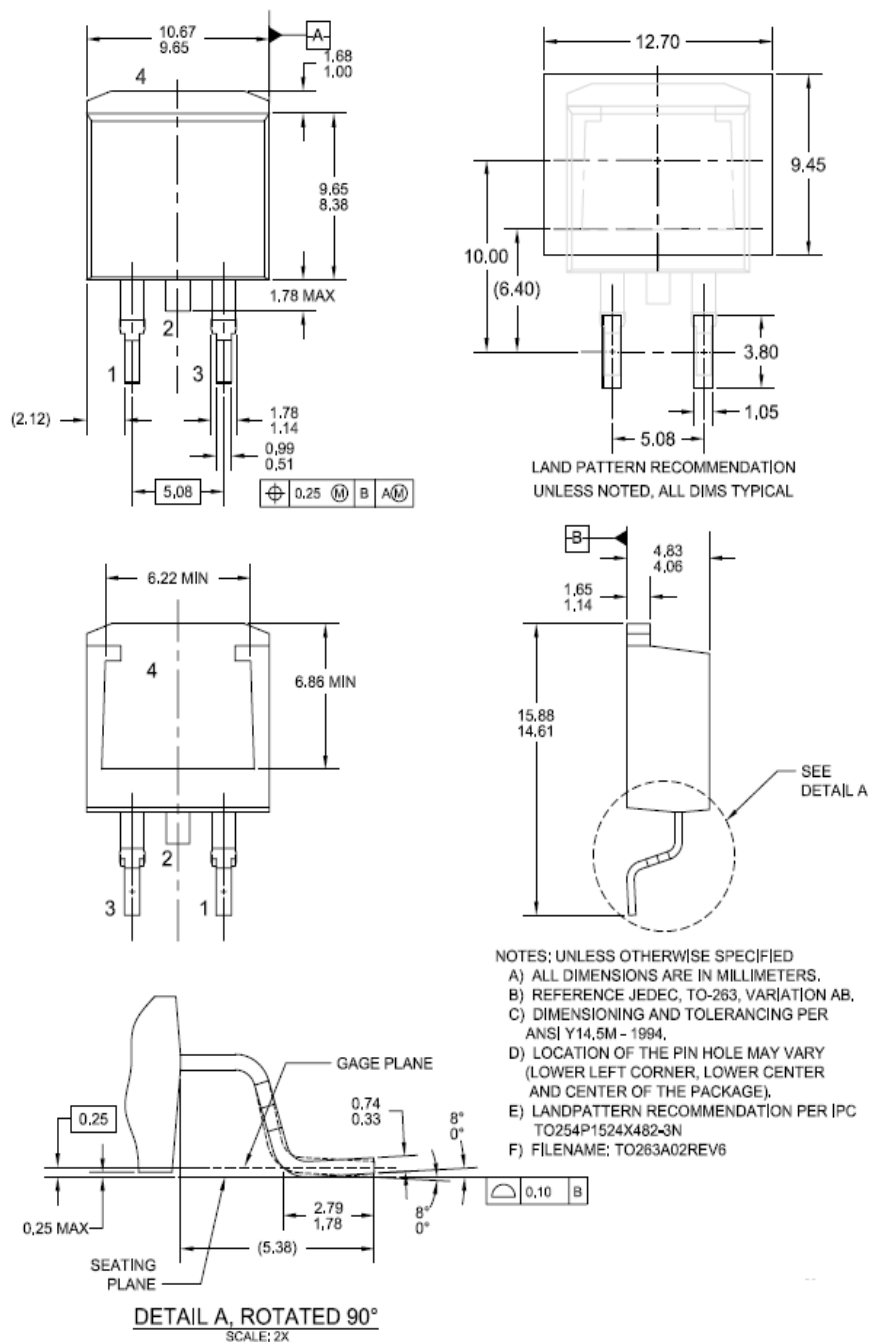


# Peak Diode Recovery dv/dt Test Circuit & Waveforms



# Mechanical Dimensions

## D<sup>2</sup>PAK



Dimensions in Millimeters

